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**Derwent Record**

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View: [Expand Details](#) Go to: [Delphion Integrated View](#) Tools: [Annotate](#) | Add to Work File: [Create new Work File](#)Derwent Title: **Mask structure of semiconductor device to prevent particles from being formed on mask**Assignee: **HYNIX SEMICONDUCTOR INC** Non-standard companyInventor: **CHOI Y K;**Accession/ **2005-328691 / 200534**

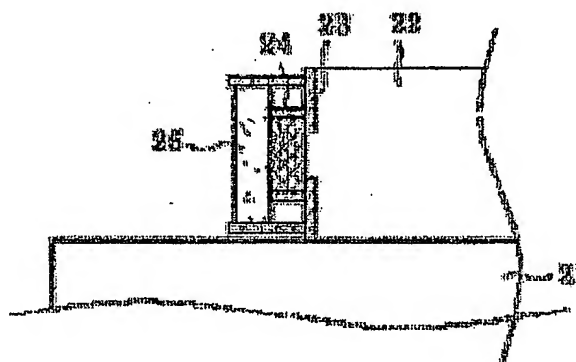
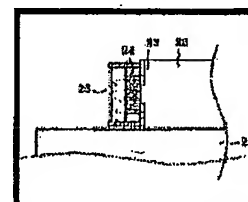
Update:

IPC Code: **H01L 21/027 ;**Derwent Classes: **U11;**Manual Codes: **U11-C04D(Masking techniques for microlithography) , U11-C04E1(Apparatus and method for photolithography)**

Derwent Abstract: (KR5001836A) **Novelty** - A mask structure of a semiconductor device is provided to prevent a foreign substance from being formed on a mask by installing a particle control filter in the entrance of a hole on a pellicle frame and by installing an ion control filter in the front of the particle control filter.

**Detailed Description** - A mask glass(21) is used to transcribe a fine pattern. A pellicle(22) and a pellicle frame(23) for supporting the pellicle are formed on the mask glass to protect the mask glass. At least one hole is formed at an end of the pellicle frame to control the flow of air. A particle control filter(24) is formed in the entrance of the hole. A chemical ion removing filter(25) is formed in the front of the particle control filter to remove chemical ions.

Images:



Dwg.1/10

Family: PDF Patent Pub. Date Derwent Update Pages Language IPC Code  
**KR5001836A** \* 2005-01-07. 200534 1 English H01L 21/027  
 Local apps.: KR2003000042177 Filed:2003-06-26 (2003KR-0042177)

Priority Number:

Application Number	Filed	Original Title
KR2003000042177	2003-06-26	

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(19) KOREAN INTELLECTUAL PROPERTY OFFICE

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## KOREAN PATENT ABSTRACTS

(11)Publication number: **1020050001836**  
(43)Date of publication of application: **07.01.2005** **A**

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(21)Applcation number:	<b>1020030042177</b>	(71)Applicant:	<b>HYNIX SEMICONDUCTOR INC.</b>
(22)Date of filling:	<b>26.06.2003</b>	(72)Inventor:	<b>CHOI, YONG KYOO</b>
(51)Int. Cl	<b>H01L 21/027</b>		

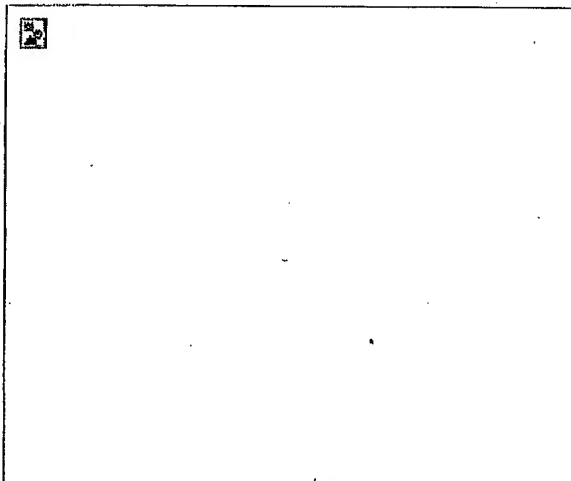
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**(54) MASK STRUCTURE OF SEMICONDUCTOR DEVICE TO PREVENT PARTICLES FROM BEING FORMED ON MASK**

(57) Abstract:

PURPOSE: A mask structure of a semiconductor device is provided to prevent a foreign substance from being formed on a mask by installing a particle control filter in the entrance of a hole on a pellicle frame and by installing an ion control filter in the front of the particle control filter.

CONSTITUTION: A mask glass(21) is used to transcribe a fine pattern. A pellicle(22) and a pellicle frame(23) for supporting the pellicle are formed on the mask glass to protect the mask glass. At least one hole is formed at an end of the pellicle frame to control the flow of air. A particle-control filter(24) is formed in the entrance of the hole. A chemical ion removing filter(25) is formed in the front of the particle control filter to remove chemical ions.



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Legal Status

Date of final disposal of an application (00000000)

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